TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

HN2S01FU

LOW VOLTAGE HIGH SPEED SWITCHING APPLICATION

HN2S01F is composed of 3 independent diodes.

Low Forward Voltage : $V_F = 0.23V (TYP.) @I_F = 5mA$

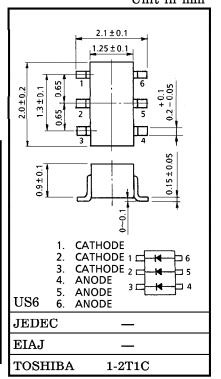
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	$ m v_{RM}$	15	V
Reverse Voltage	$V_{\mathbf{R}}$	10	V
Maximum (Peak) Forward Current	$I_{\mathbf{FM}}$	200*	mA
Average Forward Current	IO	100*	mA
Surge Current (10ms)	$I_{ ext{FSM}}$	1*	Α
Power Dissipation	P	200	mW
Junction Temperature	T_{j}	125	$^{\circ}\mathrm{C}$
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	$^{\circ}\mathrm{C}$
Operating Temperature Range	$T_{ m opr}$	-40~100	°C

* : This is the Maximum Ratings of single diode (Q1 or Q2 or Q3).

In the case of using 2 or 3 diodes, the Maximum Ratings per diode is 75% of the single diode one.

Unit in mm

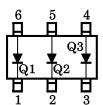


Weight: 6.2mg

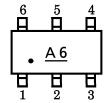
ELECTRICAL CHARACTERISTICS (Q1, Q2, Q3 COMMON Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V _F (1)	I _F =1mA		0.18	_	
	$V_{\mathbf{F}}(2)$	$I_{\mathbf{F}} = 5$ mA	_	0.23	0.30	V
	$V_{\mathbf{F}}(3)$	$I_{ m F} = 100 { m mA}$	_	0.35	0.50	
Reverse Current	$I_{\mathbf{R}}$	$V_R = 10V$	_		20	μ A
Total Capacitance	$\mathrm{C}_{\mathbf{T}}$	$V_R=0$, f=1MHz	_	20	40	рF

PIN ASSIGNMENT (TOP VIEW)



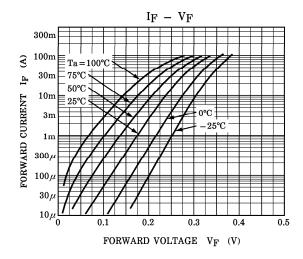
MARKING

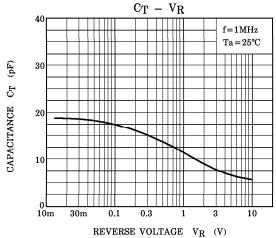


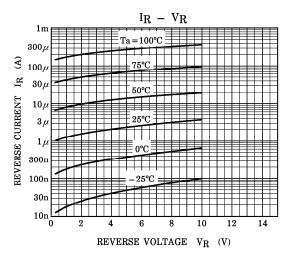
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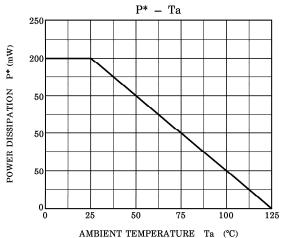
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* : Total Rating